

isc N-Channel MOSFET Transistor

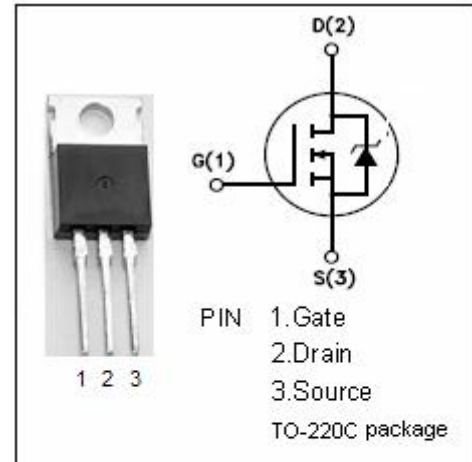
2SK1024

DESCRIPTION

- Drain Current  $-I_D=3.5A @ T_C=25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS}=900V(\text{Min})$
- Fast Switching Speed

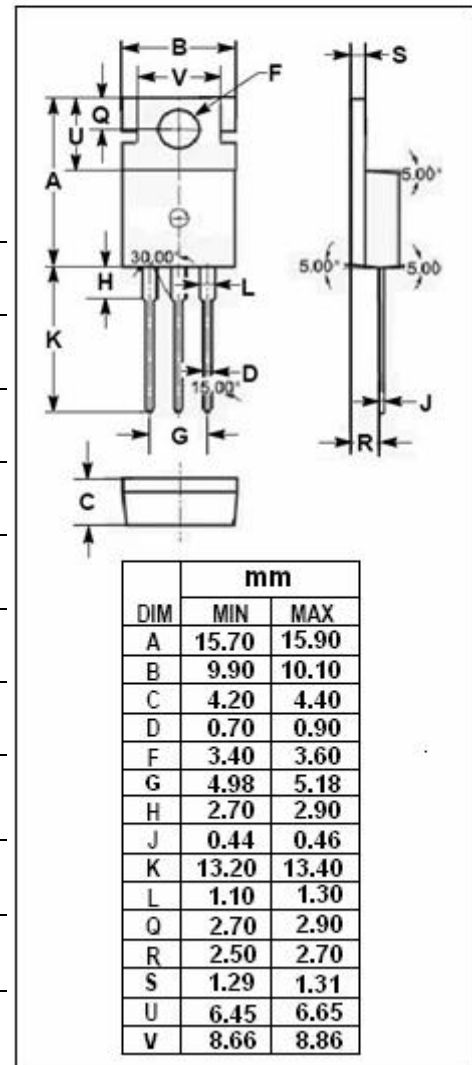
APPLICATIONS

- Designed for high voltage, high speed power switching



ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	ARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS}=0$ )	900	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current-continuous@ $TC=25^\circ C$	3.5	A
$P_{tot}$	Total Dissipation@ $TC=25^\circ C$	60	W
$T_j$	Max. Operating Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance,Junction to Case	2.08	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance,Junction to Ambient	75	$^\circ C/W$

**isc N-Channel Mosfet Transistor****2SK1024****• ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 1mA	900			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =1mA	2.5	3.5	5.0	V
R <sub>DS(on)</sub>	Drain-Source On-stage Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =2A		4.0	5.5	Ω
I <sub>GSS</sub>	Gate Source Leakage Current	V <sub>GS</sub> = ±30V; V <sub>DS</sub> = 0			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =900V; V <sub>GS</sub> = 0			1	mA
V <sub>SD</sub>	Forward On-Voltage	I <sub>S</sub> =3.5A; V <sub>GS</sub> =0		0.90	1.35	V
t <sub>r</sub>	Rise time	V <sub>GS</sub> =10V; I <sub>D</sub> =3.5A; R <sub>L</sub> =25 Ω		65	100	ns
t <sub>on</sub>	Turn-on time			95	145	ns
t <sub>f</sub>	Fall time			60	90	ns
t <sub>off</sub>	Turn-off time			170	255	ns